High Power NPN Silicon Power Transistors

These devices are designed for linear amplifiers, series pass regulators, and inductive switching applications.

Features

Forward Biased Second Breakdown Current Capability

$$\begin{split} I_{S/b} &= 3.75 \text{ Adc } @ \text{ V}_{CE} = 40 \text{ Vdc} - 2\text{N}3771 \\ &= 2.5 \text{ Adc } @ \text{ V}_{CE} = 60 \text{ Vdc} - 2\text{N}3772 \end{split}$$

• These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (Note 1)

Rating	Symbol	2N3771	2N3772	Unit
Collector-Emitter Voltage	V _{CEO}	40	60	Vdc
Collector-Emitter Voltage	V _{CEX}	50	80	Vdc
Collector-Base Voltage	V _{CB}	50	100	Vdc

Emitter-Base Voltage

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ELECTRICAL CHARACTERISTICS (T_C = 25°

2N3771, 2N3772



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